

ABSTRACT OF THE DISCLOSURE

Disclosed is a MOS-type semiconductor apparatus which adjusts the threshold voltage to a predetermined value, and lowers leak current and reduces power consumption without lowering the operating speed of transistors. The MOS-type semiconductor apparatus (1) formed using an SOI substrate in which a support substrate (3), an insulation layer (buried oxide film) (2), and a semiconductor layer are sequentially layered comprises conductors (N-wells and P-wells) beneath the insulation layer (2), and a threshold-value control circuit which compares a signal $f(soi)$ generated by an oscillator in the semiconductor apparatus to a reference signal $f(ref)$ inputted from outside, and applies bias voltages V_{sub1} and V_{sub2} to the conductors (the N-wells and P-wells) based on the difference between both signals.



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